

Supplementary

Near room temperature Thermoelectric performance improvement for Mg_2Sn

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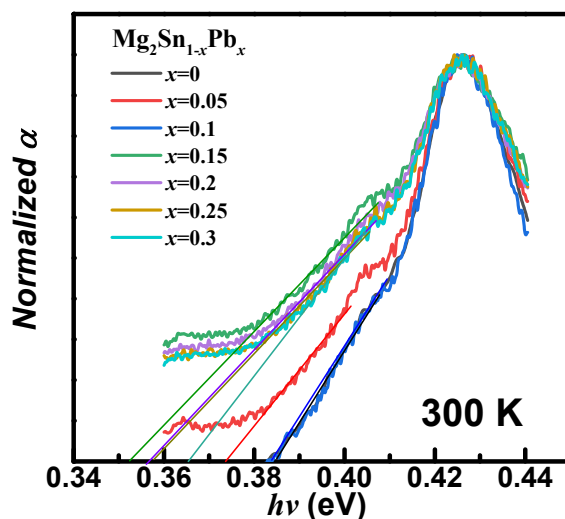


Fig. S1. The normalized inferred absorption peak of $\text{Mg}_2\text{Sn}_{1-x}\text{Pb}_x$ ($0 \leq x \leq 0.3$) samples at room temperature, indicating the decrease of band gap by Pb alloying.

The calculation process of Lorenze number:

$$L_e = \left(\frac{k_B}{e}\right)^2 \left[\frac{\left(r + \frac{7}{2}\right) F_{r+\frac{5}{2}}(\xi_e)}{\left(r + \frac{3}{2}\right) F_{r+\frac{1}{2}}(\xi_e)} - \frac{\left(r + \frac{5}{2}\right) F_{r+\frac{3}{2}}(\xi_e)}{\left(r + \frac{3}{2}\right) F_{r+\frac{1}{2}}(\xi_e)} \right]^2 \#(1-1)$$

$$L_h = \left(\frac{k_B}{e}\right)^2 \left[\frac{\left(r + \frac{7}{2}\right) F_{r+\frac{5}{2}}(\xi_h)}{\left(r + \frac{3}{2}\right) F_{r+\frac{1}{2}}(\xi_h)} - \frac{\left(r + \frac{5}{2}\right) F_{r+\frac{3}{2}}(\xi_h)}{\left(r + \frac{3}{2}\right) F_{r+\frac{1}{2}}(\xi_h)} \right]^2 \#(1-2)$$

$$S = \pm \left(\frac{\left(r + \frac{5}{2}\right) F_{r+\frac{3}{2}}(\xi_e)}{\left(r + \frac{3}{2}\right) F_{r+\frac{1}{2}}(\xi_e)} - \xi_e \right) h \#(1-3)$$

$$\xi_h = - \left(\frac{E_g}{k_B T} + \xi_e \right) \#(1-4)$$

Supplementary

$$n = 2 \left(\frac{2\pi m_e^* k_B T}{h^2} \right) F_{1/2}(\xi_e) \#(1-5)$$

$$p = 2 \left(\frac{2\pi m_h^* k_B T}{h^2} \right) F_{1/2}(\xi_h) \#(1-6)$$

$$(n_{300K} + \Delta) (p_{300K} + \Delta) = AT^3 \exp\left(-\frac{E_g}{k_B T}\right) \#(1-7)$$

Here, the r is the scattering parameter for the carrier transport based on the relaxation time approximation, where the acoustic phonon ($r = -1/2$) scattering dominants. The reduced Fermi energy ξ_e and ξ_h near room temperature could be estimated from the Seebeck coefficient on the basis of single band approximation formula Eq. (1-3 and 1-4). The reduced Fermi energy $\xi(T)$ at the higher temperature is obtained by Eq. (1-4~1-7) at a given temperature.

m_e^* was obtained from the measured carrier concentration and Seebeck coefficient of $\text{Mg}_{2.03}\text{Sn}_{1-x}\text{Pb}_x$ in this study, while $m_h^* = 1.3 m_0$ was used.

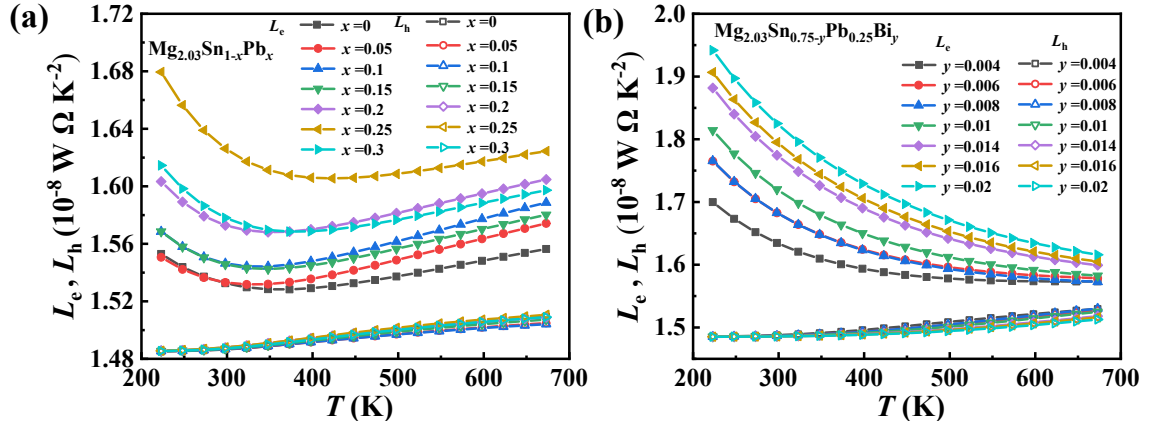


Fig. S2. The temperature dependent L_e , L_h of $\text{Mg}_{2.03}\text{Sn}_{1-x}\text{Pb}_x$ ($0 \leq x \leq 0.05$) (a) and $\text{Mg}_{2.03}\text{Sn}_{0.75-y}\text{Pb}_{0.25}\text{Bi}_y$ ($0 \leq y \leq 0.02$) (b) samples in this work.

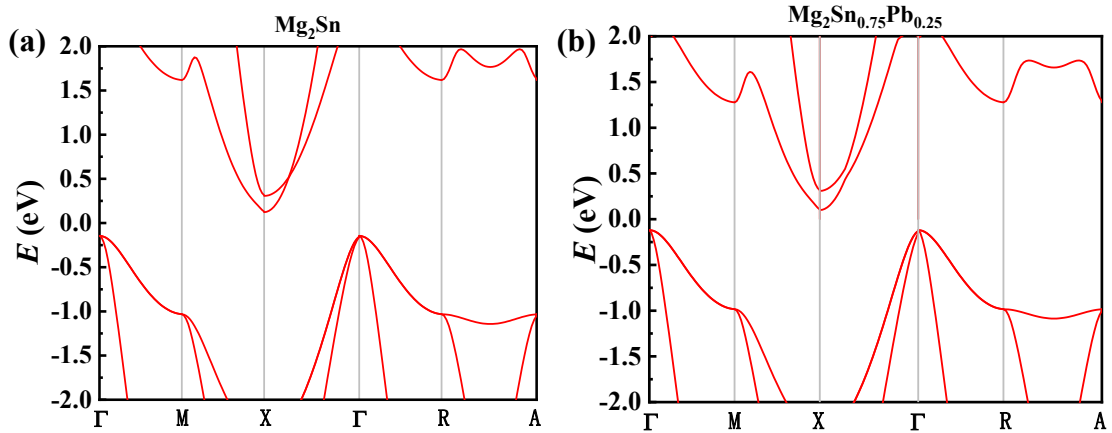


Fig. S3. The first-principle calculated band structure of Mg_2Sn (a) and $\text{Mg}_2\text{Sn}_{0.75}\text{Pb}_{0.25}$ (b) .